**U2891B** 

## 2.5 GHz Quadrature Up-Converter

#### **Description**

The U2891B is a silicon monolithic IC made with TELE-FUNKEN's advanced UHF process. The IC consists of a 500 MHz I/Q quadrature modulator and a 2.5 GHz mixer. Both parts can be connected via an external filter in order to suppress harmonics and spurious products. The device features 3 V operation, a low current consumption and furthermore two separate power-down functions for mod-

ulator and mixer. The RF ports are single ended and the device can be operated adjustment free, but for optimization also two pins for phase adjustment are provided. These features and the double conversion concept of U2891B make this device perfectly suited for all digital radio applications from 900 MHz up to 2.5 GHz (e.g., GSM, DCS 1800, JDC, PHP and WLAN).

#### **Features**

- Low power consumption: 25 mA / 3 V (typical at –8 dBm output level)
- 2.5 GHz output frequency
- Excellent sideband suppression by means of duty cycle regeneration and 90° phase control
- Separate power-down mode for modulator and mixer
- Low LO input level: -10 dBm (typical)
- LO and RF port 50-Ω single-ended

#### **Benefits**

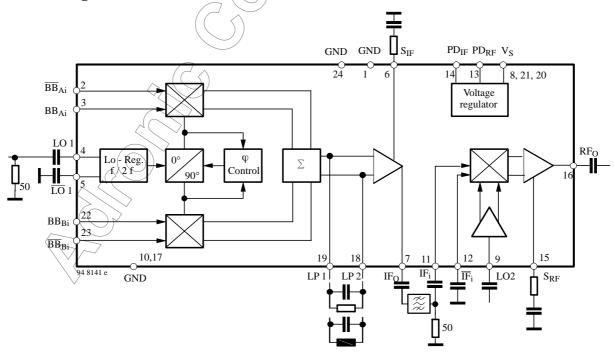
- Extended talk time due to increased battery life
- Few external components results in cost and board space-saving
- Adjustment free, hence saves time and cost
- One TX Platform for different systems
- Reduced costs and space for battery (3-V operation)

Case: SSO-24 package

#### **Ordering Information:**

U2891B-AFS, U2891B-AFSG3 (see page 5)

## **Block Diagram**



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## **Pin Description**

GND	1	24	GND
$\overline{BB}_{Ai}$	2	23	$\overline{BB}_{Bi}$
$BB_{Ai}$	3	22	BB <sub>Bi</sub>
LO 1	4	21	$v_{s}$
TO 1	5	20	$v_{s}$
$S_{IF}$	6	19	LP 1
$IF_O$	7	18	LP 2
$V_{S}$	8	17	GND
LO 2	9	16	] RF <sub>O</sub>
GND	10	15	$]$ $S_{RF}$
$IF_i$	11	14	PD <sub>IF</sub>
$\overline{\text{IF}}_i$	12	13	PDRF
	_	94 8581 e	

		<u> </u>
Pin	Symbol	Function
1	GND	Ground
2	$\overline{\mathrm{BB}}_{\mathrm{Ai}}$	Baseband input B inverse
3	$BB_{Ai}$	Baseband input B
4	LO 1	LO 1 input
5	TO 1	LO 1 input/inverse
6	S <sub>IF</sub>	Output symmetry IF
7	IFO	IF output )
8	$V_{S}$	Supply voltage
9	LO 2	LO 2 input
10	GND	Ground
11	IF₁ ⟨∽	IF input
12	ĪF <sub>i</sub> ←	IF input inverse
13	PDRE	Power-down RF
14	PDIF	Power-down IF
15	$(S_{RE})$	Output symmetry RF
16	$\bigcirc RF_0$	RF output
17 <	GND	Ground
18	LP 2	Filter and IF level
()	)	adjustment
19	LP 1	Filter and IF level
		adjustment
20	$V_{S}$	Supply voltage
21	$V_{S}$	Supply voltage
22	$BB_{Bi}$	Baseband input B
23	$\overline{\mathrm{BB}}_{\mathrm{Bi}}$	Baseband input B inverse
24	GND	Ground

# **Absolute Maximum Ratings**

Parameters	Symbol	Value	Unit
Supply voltage Pins 8, 20 and 21	$V_S, V_{SRF}$	6	V
Input voltage Pins 2, 3, 4, 5, 9, 11, 12, 22 and 23	V <sub>i</sub>	0 to V <sub>S</sub>	V
Junction temperature	$T_{j}$	125	°C
Storage temperature range	T <sub>stg</sub>	-40 to +125	°C

# **Operating Range**

Parameters	Symbol	Value	Unit
Supply voltage Pins 8, 20 and 21	$V_{S}, V_{SRF}$	2.7 to 5.5	V
Ambient temperature range	T <sub>amb</sub>	-40 to +85	°C

# Thermal Resistance

Parameters		Symbol	Value	Unit
Junction ambient	SSO-24	R <sub>thja</sub>	140	K/W

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#### **Electrical Characteristics: General Data**

Parameters	Test Conditions / Pin	Symbol	Min.	Тур.	Max.	Unit
Power supply				^		
Supply voltage range	Pin 8, 20 and 21	V <sub>S</sub> , V <sub>SRF</sub>	2.7		5,5	V
Supply current	Pin 8, 20 and 21, $V_S = 3 \text{ V}$	I <sub>S</sub> , I <sub>SRF</sub>		25 (		mA

## **Electrical Characteristics: I/Q Modulator**

Test conditions (unless otherwise specified):  $V_S = 3$  V,  $T_{amb} = 25$ °C, referred to test circuit. System impedance  $Z_O = 50$   $\Omega$ ,  $f_{LO1} = 100$  MHz,  $P_{LO1} = -10$  dBm.

Parameters	Test Conditions / Pin	Symbol	Min.	Тур.	Max.	Unit
	Test Conditions / Tim	Symbol	NIII.	Typ.	wax.	Oilit
IF output Pin 7	1	T	~~~		T	
Output level	$R_{LP} = \infty$	P <sub>IFo</sub>		- 8		dBm
LO1 suppression		LO <sub>RFo</sub>	Š	40		dB
Voltage standing wave ratio		VSWR <sub>IF9</sub> /	() ·	1.4	2	
Sideband suppression		SBS <sub>IFQ</sub>		45		dB
Baseband inputs Pins 2,	3, 22 and 23	4				
Input voltage range (differential)		V <sub>BBi</sub>		500	900	mVpp
Input impedance		$Z_{BBi}$		150		kΩ
Input frequency		$\int$ $f_{ m BBi}$			200	MHz
LO1 input Pins 4 and 5						
Frequency range		$f_{LOi}$	30		500	MHz
Input level 1)		$P_{LOi}$		-10	-2	dBm
Input impedance		$Z_{iLO}$		tbd.		Ω
Duty cycle range		DCR <sub>LO1</sub>	0.4		0.6	
Power-down mode						
Supply current	$V_{PD} \le 0.5 \text{ V Pin } 14$	$I_{\mathrm{PD}}$		<5		μΑ
Settling time	C <sub>SPD</sub> 100 pF, C <sub>LO</sub> = 100 pF, C <sub>RFo</sub> = 1 nF	$t_{S}$		10		μs
Power down voltage Pin 14						
"Power on"	$V_S = 3.5 \text{ to } 5.5 \text{ V}$ $V_S = 2.7 \text{ to } 3.5 \text{ V}$	V <sub>PON</sub>	$V_S - 0.5$ $V_S$		V <sub>S</sub> +0.5 V <sub>S</sub> +0.5	V V
"Power down"		V <sub>PDN</sub>			1	V
Power down current	Power on Power down	I <sub>PON</sub> I <sub>PDN</sub>		0.15 < 1		mA μA

Note:

<sup>1)</sup> Required LO level is a function of the LO frequency

#### **Electrical Characteristics: Mixer**

 $V_S = 3 \text{ V}, f_{LO2} = 800 \text{ MHz}, f_{IF} = 100 \text{ MHz}, P_{LO2} = -10 \text{dBm}, \text{ system impedance Zo} = 50 \Omega, T_{amb} = 25 ^{\circ}\text{C}$  reference point Pin 10, unless otherwise specified

Parameters	Test Conditions / Pin	Symbol	Min.	Тур.	Max.	Unit
Operating frequencies	•					
RF <sub>O</sub> frequency	Pin 16	RFO	50	7(	2500	MHz
LO2 frequency	Pin 9	$f_{LO2}$	50		2500	MHz
Isolation		•		$(\langle \langle \rangle)$		
LO2 spurious at RF <sub>o</sub>	Pin 9–16 P <sub>iLO</sub> = –10 to 0 dBm	IS <sub>LO2</sub> -RFo		-30		dBm
RF <sub>o</sub> to LO2	Pin 16–9	IS <sub>RFo-LO2</sub>		tbd.		dB
Output level	12.22.24.7	KI 0-LO2	M	7)		
Output compression point	Pin 16 $R_{Po} = \infty$	$CP_0 - 1 dB$		_7		dBm
Input level	10	1 - 0	7			
Input compression point 1)	Pins 11 and 12	$CP_i - 1dB/$		-15		dBm
Input LO2	Pin 9	P <sub>LO2</sub>	<i>V</i> (5)	-10		dBm
Third order input intercept point <sup>1)</sup>	Pins 11 and 12	P <sub>iIIP3</sub>	>	-6		dBm
Voltage standing wave ratio	(VSWR)					
Input IF	Pins 11 and 12	VSWR <sub>IFi</sub>		tbd.		
Input LO2	Pin 9	VSWR <sub>LO2</sub>		tbd.		
Output RF	Pin 16	VSWR <sub>RF</sub>		tbd.		
Conversion power gain	$R_L = 50 \Omega$	PG <sub>C</sub>		9		dB
Noise Figure (SSB) <sup>2)</sup>	$P_{iLO} = -6 \text{ dBm}$	NF50		13		dB
Power-down mode						
Supply current	$V_{PD} \le 0.5 \text{ V Pin } 13$	$I_{PD}$		<5		μΑ
Settling time	C <sub>SPD</sub> 100 pF, C <sub>LO</sub> = 100 pF, C <sub>RFo</sub> = 1 nF	$t_{\mathrm{S}}$		10		μs
Power down voltage Pin 13						
"Power on"	$V_S = 3.5 \text{ to } 5.5 \text{ V}$ $V_S = 2.7 \text{ to } 3.5 \text{ V}$	V <sub>PON</sub>	$V_S - 0.5$ $V_S$		V <sub>S</sub> +0.5 V <sub>S</sub> +0.5	V V
"Power down"		V <sub>PDN</sub>	5		1	V
Power down current	Power on Power down	I <sub>PON</sub> I <sub>PDN</sub>		0.15 < 1		mA μA

#### Note:

1) with 50  $\Omega$  termination resistor at Pin 11

2) without termination resistor

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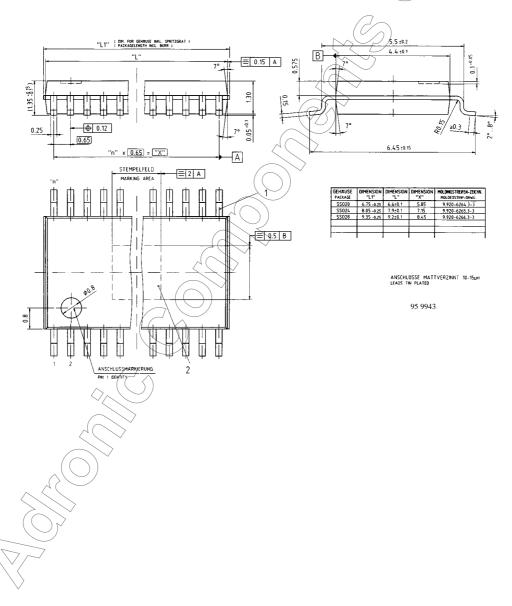
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## **Ordering Information**

Extended Type Number		Package	Remarks
	U2891B-AFS	SSO24	Rail, MOQ 690 pcs.
	U2891B-AFSG3	SSO24	Tape & reel, MOQ 4000 pcs.

### **Dimensions in mm**

Package: SSO-24



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#### **Ozone Depleting Substances Policy Statement**

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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